

## **AMENDMENTS TO THE SPECIFICATION:**

Please replace the first paragraph of Page 8 with the following amended paragraph:

According to another disclosed class of innovative embodiments, there is provided: A fabrication method, comprising the steps of: forming a first layer of silicon at least partially overlying a substantially monolithic body of semiconductor material; forming a layer of nitride at least partially overlying said first layer of silicon; forming a layer of oxide at least partially overlying said first layer of silicon; after said steps of forming said layer of nitride and forming said layer of oxide, ~~but prior to performing any other steps,~~ forming a second layer of silicon at least partially overlying said layer of oxide, said layer of nitride, and said first layer of silicon; wherein only two layers are present between said first layer of silicon and said second layer of silicon.